
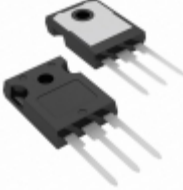
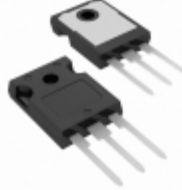
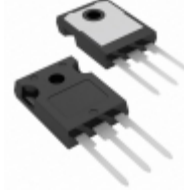


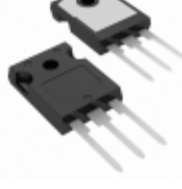


	<h2>HGTG11N120CND</h2>
	<p>Hersteller-Teilenummer: HGTG11N120CND</p> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <p>Teil der Beschreibung: IGBT 1200V 43A 298W TO247</p> <p>Datenblätter:  HGTG11N120CND.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 8814 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	HGTG11N120CND
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	IGBT 1200V 43A 298W TO247
Kategorie	Diskrete Halbleiterprodukte > Transistoren-IGBTs
Teilstatus	8814 pcs Stock
detaillierte Beschreibung	IGBT NPT 1200V 43A 298W Through Hole TO-247
Serie	-
Eingabetyp	Standard
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Leistung - max	298W
Verpackung / Gehäuse	TO-247-3
Supplier Device-Gehäuse	TO-247
Rückwärts-Erholzeit (Trr)	70ns
Strom - Kollektor (Ic) (max)	43A
Spannung - Kollektor-Emitter-Durchbruch (max)	1200V
IGBT-Typ	NPT
VCE (on) (Max) @ Vge, Ic	2.4V @ 15V, 11A
Strom - Collector Pulsed (Icm)	80A
Schaltenergie	950µJ (on), 1.3mJ (off)
Gate-Ladung	100nC
Td (ein / aus) bei 25 ° C	23ns/180ns
Testbedingung	960V, 11A, 10 Ohm, 15V
Verpackung	Tube
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)



















































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Sie können auch interessiert sein:

 <p>HGTG12N60A4 Fairchild/ON Semiconductor IGBT 600V 54A 167W TO247</p>	 <p>HGTG11N120CND Fairchild/ON Semiconductor IGBT 1200V 43A 298W TO247</p>	 <p>HGTG10N120BND Fairchild/ON Semiconductor IGBT 1200V 35A 298W TO247</p>	 <p>HGTG12N60A4 AMI Semiconductor / ON Semiconductor IGBT 600V 54A 167W TO247</p>
 <p>HGTG120N60B3D HAR HAR TO-247</p>	 <p>HGTG11N120CN Fairchild/ON Semiconductor IGBT 1200V 43A 298W TO247</p>	 <p>HGTG11N120CN AMI Semiconductor / ON Semiconductor IGBT 1200V 43A 298W TO247</p>	 <p>HGTG10N120BND AMI Semiconductor / ON Semiconductor IGBT 1200V 35A 298W TO247</p>

heiße Teile

Mehr

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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